ABSTRACT

A method of testing ion implantation equipment verifies the level of ion implantation energy. The method includes implanting first conductive ions in an implantation region in a semiconductor substrate, implanting second conductive ions, having valence different from that of the first conductive ions, in the implantation region so as to produce a second well, and subsequently measuring a sheet resistance of the semiconductor substrate. The implanting of the second conductive ions may be carried out while varying the level of the ion implantation energy. By forming a twin well in this way, and then measuring the sheet resistance, the value of the sheet resistance can be precisely correlated to the amount of energy used to form a well.